

## Features

- ✧ Small hermetically sealed glass SMD package
- ✧ High switching speed: max. 4 ns
- ✧ Continuous reverse voltage:  
Max. 75V
- ✧ Repetitive peak reverse voltage:  
Max. 100V
- ✧ Repetitive peak forward current:  
Max. 450mA

Dimensions in inches and (millimeters)

## Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

### Maximum Ratings

Type Number	Symbol	Value	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Continuous Reverse Voltage	$V_R$	75	V
Continuous Forward Current Fig. 2, (Note 1)	$I_F$	200	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repetitive Peak Forward Current Square wave: $T_J=25^\circ\text{C}$ Prior to surge: see Fig. 4 $t=1\mu\text{s}$ $t=1\text{ms}$ $t=1\text{s}$	$I_{FSM}$	4 1 0.5	A
Total Power Dissipation $T_{amb}=25^\circ\text{C}$ , (Note 1)	$P_{tot}$	500	mW
Operating Junction Temperature	$T_J$	200	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to + 200	$^\circ\text{C}$

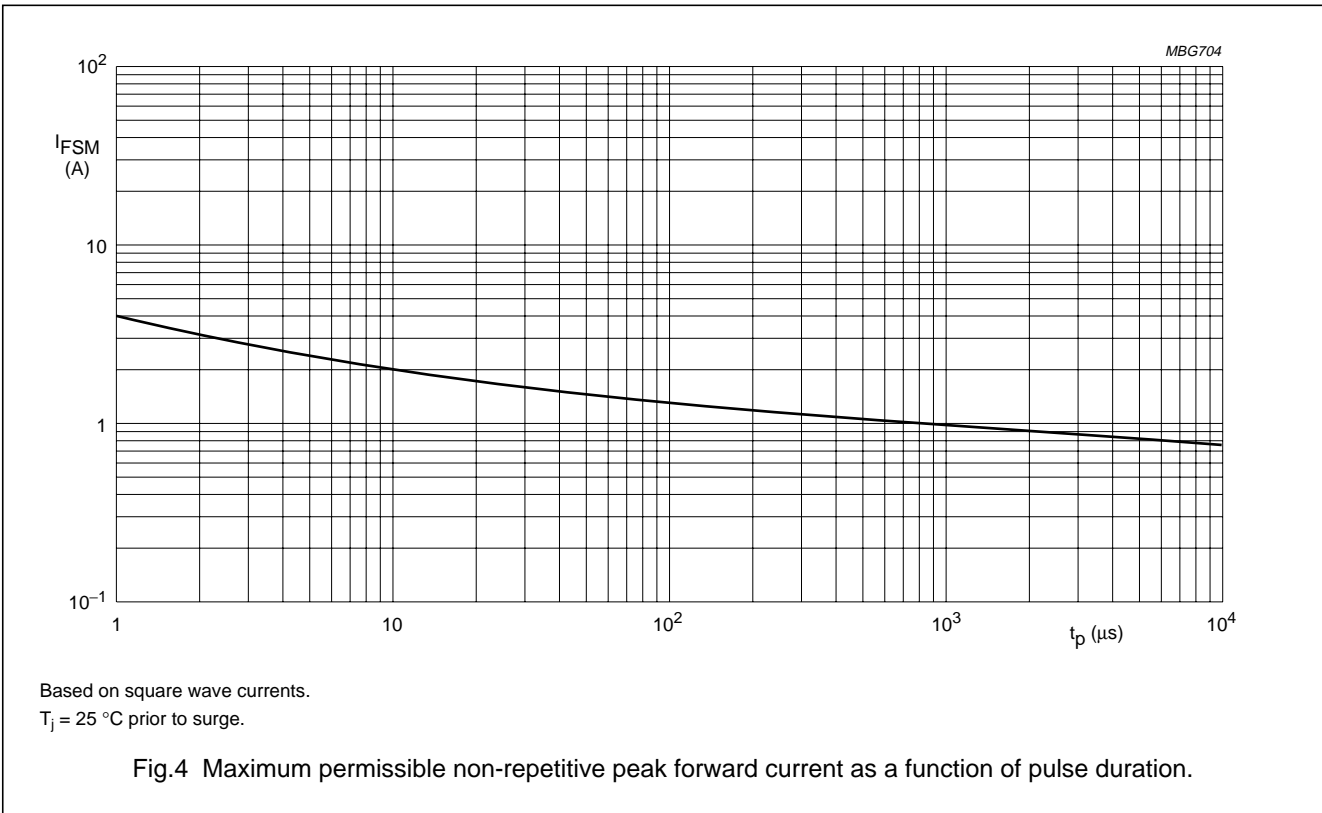
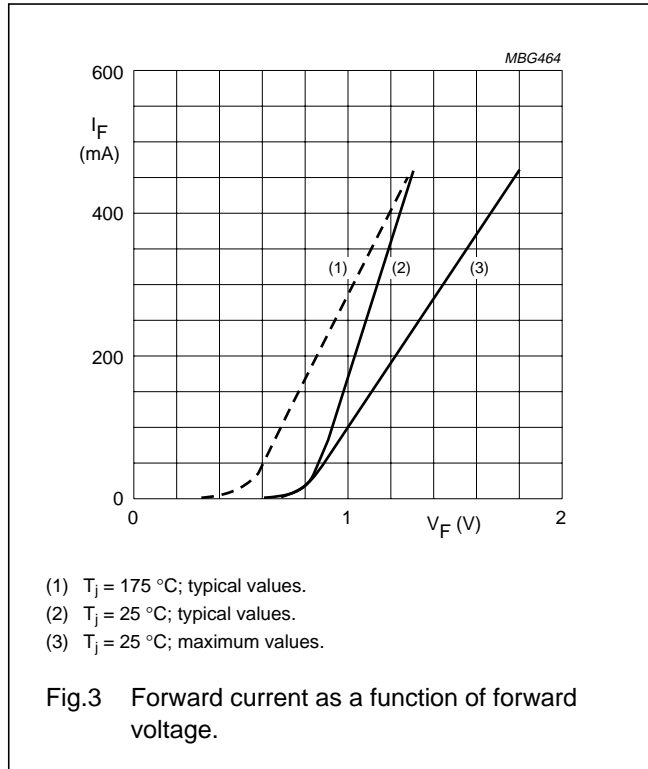
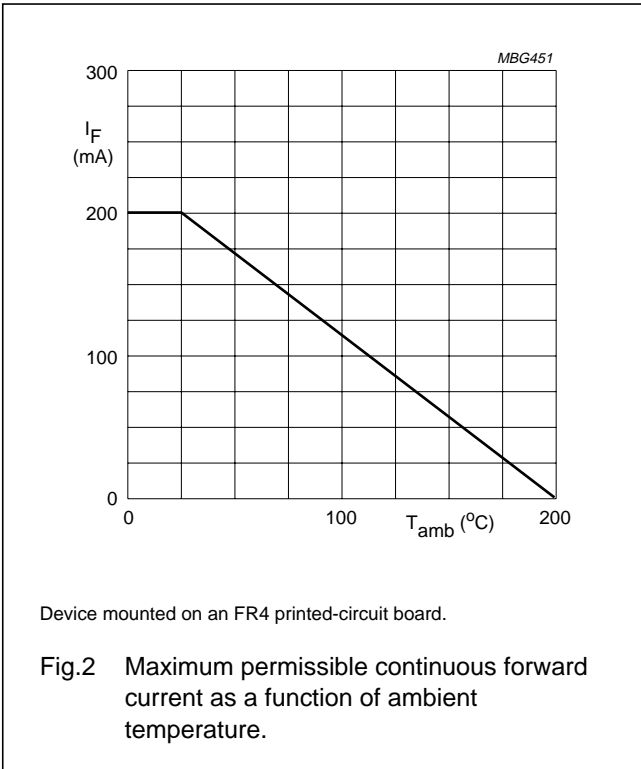
### Electrical Characteristics

Type Number	Symbol	Min	Max	Units
Forward Voltage See Fig. 3 $I_F=5.0\text{mA}$ $I_F=10\text{mA}$ $I_F=100\text{mA}$	$V_F$	0.62 - -	0.72 1.0 1.0	V
Reverse Leakage Current $V_R=20\text{V}$ see Fig. 5 $V_R=20\text{V } T_J=150^\circ\text{C}$ $V_R=20\text{V } T_J=100^\circ\text{C}$	$I_R$	- - -	25 50 3	nA uA uA
Junction Capacitance $V_R=0$ , $f=1.0\text{MHz}$	$C_j$	-	4.0	pF
Reverse Recovery Time (Note 2)	$t_{rr}$	-	4.0	nS
Forward Recovery Voltage $I_F=50\text{mA}$ , $t_r=20\text{ns}$	$V_{fr}$	-	2.5	V

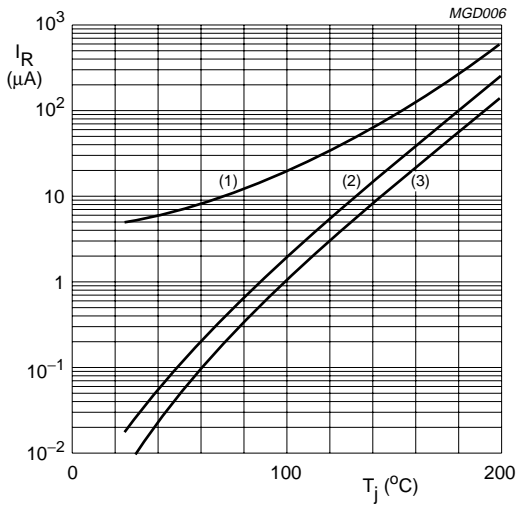
Notes: 1. Device Mounted on an FR4 printed-circuit board.

2. Reverse Recovery Test Conditions:  $I_F=10\text{mA}$ ,  $I_R=60\text{mA}$ ,  $R_L=100\Omega$ ,  $I_{RR}=1\text{mA}$

RATINGS AND CHARACTERISTIC CURVES (LL4148L)

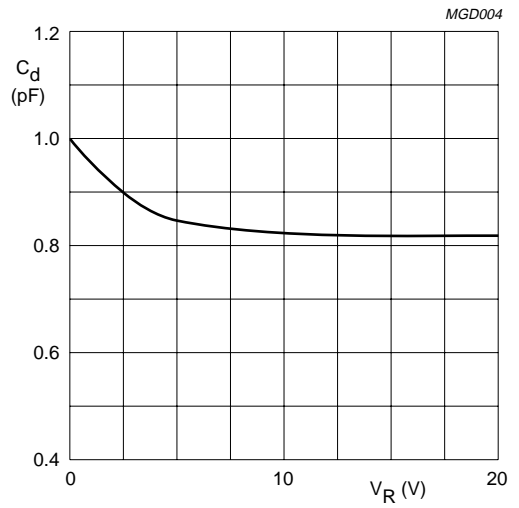


RATINGS AND CHARACTERISTIC CURVES (LL4148L)



- (1)  $V_R = 75$  V; maximum values.
- (2)  $V_R = 75$  V; typical values.
- (3)  $V_R = 20$  V; typical values.

Fig.5 Reverse current as a function of junction temperature.



$f = 1$  MHz;  $T_j = 25$  °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.